MCM6227A

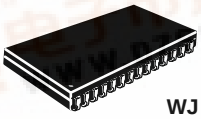
1M x 1 Bit Static Random Access Memory

The MCM6227A is a 1,048,576 bit static random–access memory organized as 1,048,576 words of 1 bit, fabricated using high–performance silicon–gate CMOS technology. Static design eliminates the need for external clocks or timing strobes while CMOS circuitry reduces power consumption and provides for greater reliability.

The MCM6227A is equipped with a chip enable ($\overline{E}$) pin. In less than a cycle time after $\overline{E}$ goes high, the part enters a low–power standby mode, remaining in that state until $\overline{E}$ goes low again.

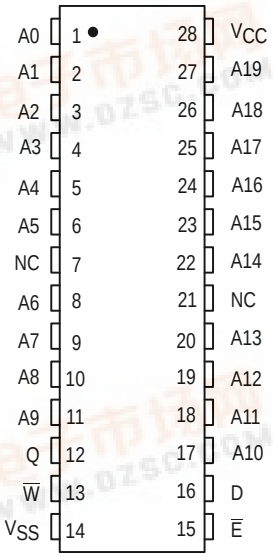
The MCM6227A is available in 400 mil, 28–lead surface–mount SOJ packages.

- Single 5 V ± 10% Power Supply
- Fast Access Times: 20, 25, 35, and 45 ns
- Equal Address and Chip Enable Access Times
- Input and Output are TTL Compatible
- Three–State Output
- Low Power Operation: 160/140/130/120 mA Maximum, Active AC



WJ PACKAGE
400 MIL SOJ
CASE 810–03

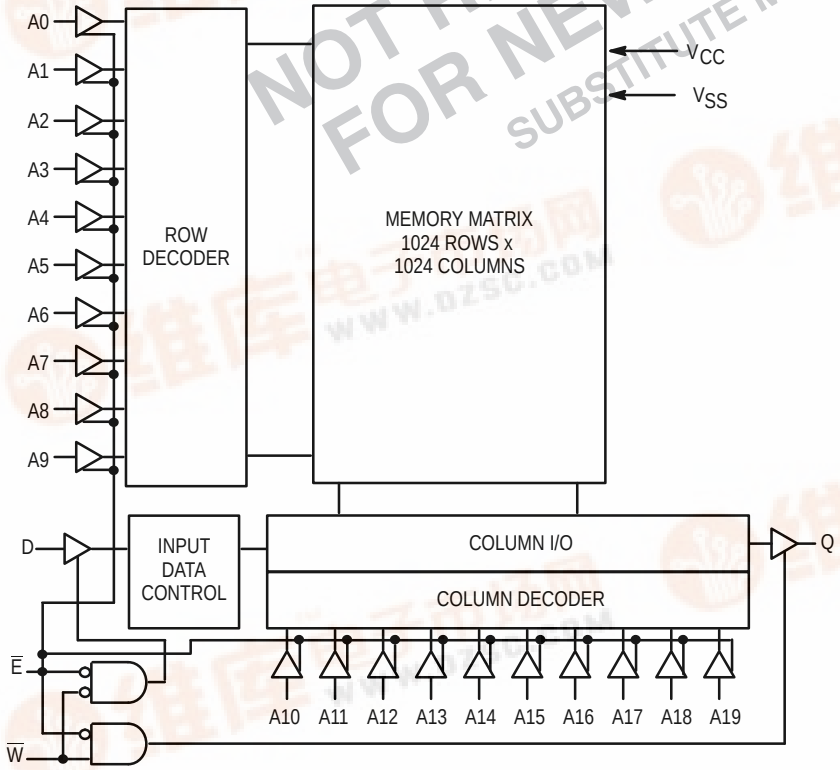
PIN ASSIGNMENT



PIN NAMES

A0 – A19	Address Inputs
$\overline{W}$	Write Enable
$\overline{E}$	Chip Enable
D	Data Input
Q	Data Output
NC	No Connection
V_{CC}	+ 5 V Power Supply
V_{SS}	Ground

BLOCK DIAGRAM



MCM6227A TRUTH TABLE

$\overline{E}$	$\overline{W}$	Mode	I/O Pin	Cycle	Current
H	X	Not Selected	High–Z	—	I_{SB1}, I_{SB2}
L	H	Read	D_{out}	Read	I_{CCA}
L	L	Write	High–Z	Write	I_{CCA}

H = High, L = Low, X = Don't Care

ABSOLUTE MAXIMUM RATINGS (See Note)

Rating	Symbol	Value	Unit
Power Supply Voltage Relative to V_{SS}	V_{CC}	– 0.5 to 7.0	V
Voltage Relative to V_{SS} for Any Pin Except V_{CC}	V_{in}, V_{out}	– 0.5 to V_{CC} + 0.5	V
Output Current	I_{out}	± 20	mA
Power Dissipation	P_D	1.1	W
Temperature Under Bias	T_{bias}	– 10 to + 85	°C
Operating Temperature	T_A	0 to + 70	°C
Storage Temperature	T_{stg}	– 55 to + 150	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to these high–impedance circuits.

This CMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow of at least 500 linear feet per minute is maintained.

DC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V ± 10%, T_A = 0 to 70°C, Unless Otherwise Noted)

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage (Operating Voltage Range)	V_{CC}	4.5	5.5	V
Input High Voltage	V_{IH}	2.2	V_{CC} + 0.3**	V
Input Low Voltage	V_{IL}	– 0.5*	0.8	V

* V_{IL} (min) = – 0.5 V dc; V_{IL} (min) = – 2.0 V ac (pulse width ≤ 20 ns).
** V_{IH} (max) = V_{CC} = 0.3 V dc; V_{IH} (max) = V_{CC} + 2 V ac (pulse width ≤ 20 ns).

DC CHARACTERISTICS AND SUPPLY CURRENTS

Parameter	Symbol	Min	Typ*	Max	Unit
Input Leakage Current (All Inputs, V_{in} = 0 to V_{CC})	$I_{lkg(I)}$	—	—	± 1	µA
Output Leakage Current ($\overline{E}$ = V_{IH}, V_{out} = 0 to V_{CC})	$I_{lkg(O)}$	—	—	± 1	µA
AC Active Supply Current (I_{out} = 0 mA, V_{CC} = max)	I_{CCA}				mA
MCM6227A–20: t_{AVAV} = 20 ns		—	120	160	
MCM6227A–25: t_{AVAV} = 25 ns		—	110	140	
MCM6227A–35: t_{AVAV} = 35 ns		—	100	130	
MCM6227A–45: t_{AVAV} = 45 ns		—	90	120	
AC Standby Current (V_{CC} = max, $\overline{E}$ = V_{IH}, f = f_{max})	I_{SB1}	—	7	20	mA
CMOS Standby Current ($\overline{E}$ ≥ V_{CC} – 0.2 V, V_{in} ≤ V_{SS} + 0.2 V or ≥ V_{CC} – 0.2 V, V_{CC} = max, f = 0 MHz)	I_{SB2}	—	4	15	mA
Output Low Voltage (I_{OL} = + 8.0 mA)	V_{OL}	—	—	0.4	V
Output High Voltage (I_{OH} = – 4.0 mA)	V_{OH}	2.4	—	—	V

* Typical values are measured at 25°C, V_{CC} = 5 V.

CAPACITANCE (f = 1.0 MHz, dV = 3.0 V, T_A = 25°C, Periodically Sampled Rather Than 100% Tested)

Characteristic		Symbol	Typ	Max	Unit
Input Capacitance	All Inputs Except Clocks and D, Q $\overline{E}$ and $\overline{W}$	C_{in}	4 5	6 8	pF
Input and Output Capacitance	D, Q	C_{in}, C_{out}	5	8	pF

AC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V ± 10%, T_A = 0 to + 70°C, Unless Otherwise Noted)

Input Pulse Levels . . . . . 0 to 3.0 V
Input Rise/Fall Time . . . . . 2 ns
Input Timing Measurement Reference Level . . . . . 1.5 V
Output Timing Measurement Reference Level . . . . . 1.5 V
Output Load . . . . . See Figure 1A

READ CYCLE TIMING (See Notes 1 and 2)

Parameter	Symbol	6227A–20		6227A–25		6227A–35		6227A–45		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max		
Read Cycle Time	t_{AVAV}	20	—	25	—	35	—	45	—	ns	2,3
Address Access Time	t_{AVQV}	—	20	—	25	—	35	—	45	ns	
Enable Access Time	t_{ELQV}	—	20	—	25	—	35	—	45	ns	4
Output Hold from Address Change	t_{AXQX}	5	—	5	—	5	—	5	—	ns	
Enable Low to Output Active	t_{ELQX}	5	—	5	—	5	—	5	—	ns	5, 6, 7
Enable High to Output High–Z	t_{EHQZ}	0	9	0	10	0	12	—	18	ns	5, 6, 7
Power Up Time	t_{ELICCH}	0	—	0	—	0	—	0	—	ns	
Power Down Time	t_{EHICCL}	—	20	—	25	—	35	—	45	ns	

NOTES:
1. $\overline{W}$ is high for read cycle.
2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
3. All timings are referenced from the last valid address to the first transitioning address.
4. Addresses valid prior to or coincident with $\overline{E}$ going low.
5. At any given voltage and temperature, t_{EHQZ} max is less than t_{ELQX} min, both for a given device and from device to device.
6. Transition is measured ± 500 mV from steady–state voltage with load of Figure 1B.
7. This parameter is sampled and not 100% tested.
8. Device is continuously selected ($\overline{E} \le V_{IL}$).

AC TEST LOADS

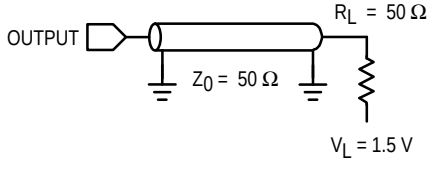


Figure 1A

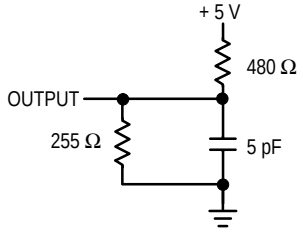
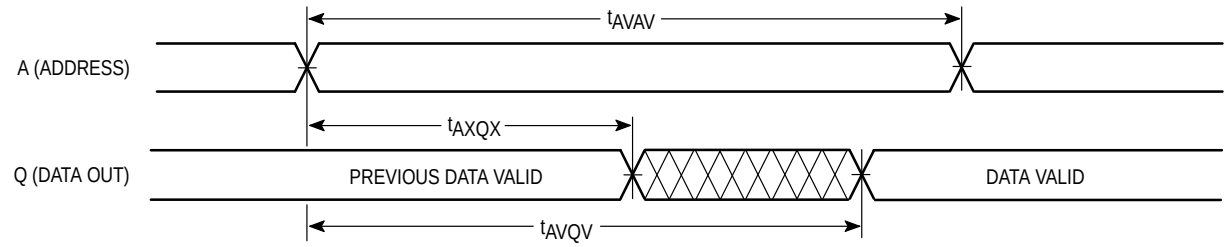


Figure 1B

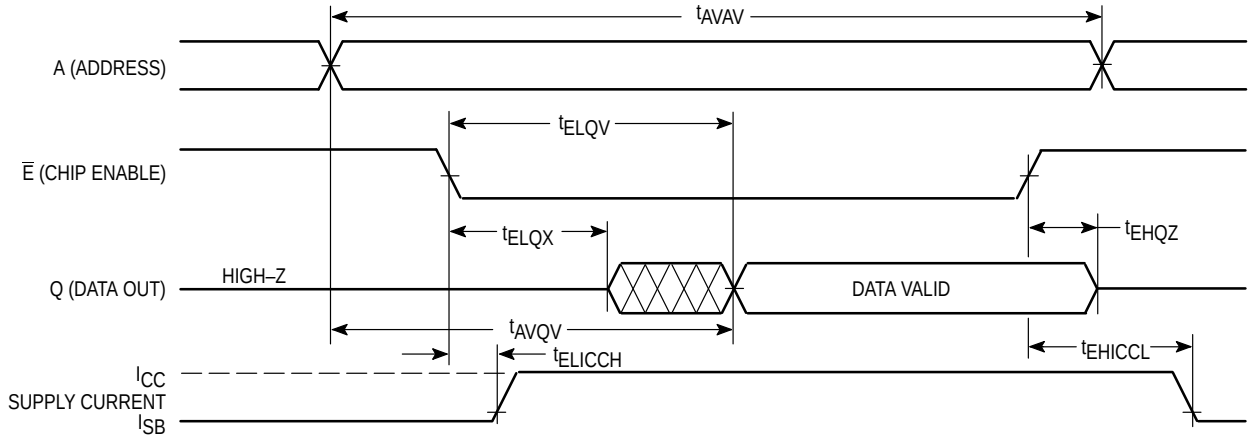
TIMING LIMITS

The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

READ CYCLE 1 (See Notes 1, 2, and 8)



READ CYCLE 2 (See Note 4)

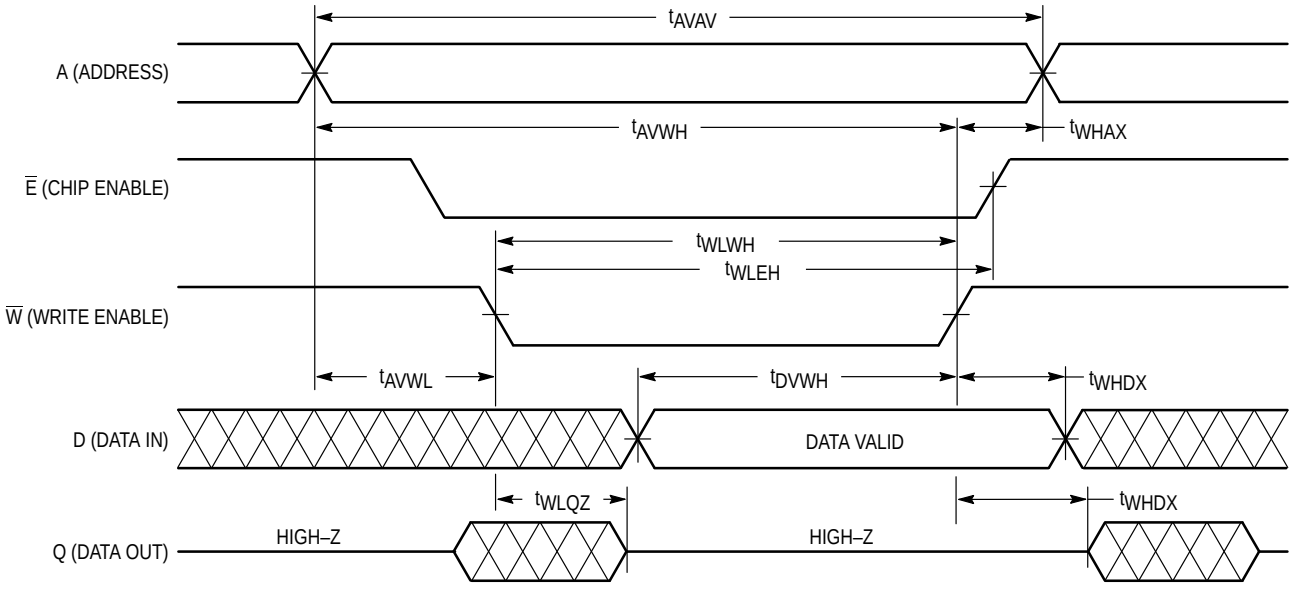


WRITE CYCLE 1 ($\overline{W}$ Controlled, See Notes 1 and 2)

Parameter	Symbol	6227A–20		6227A–25		6227A–35		6227A–45		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max		
Write Cycle Time	t_{AVAV}	20	—	25	—	35	—	45	—	ns	3
Address Setup Time	t_{AVWL}	0	—	0	—	0	—	0	—	ns	
Address Valid to End of Write	t_{AVWH}	15	—	17	—	20	—	25	—	ns	
Write Pulse Width	t_{WLWH}, t_{WLEH}	15	—	17	—	20	—	25	—	ns	
Data Valid to End of Write	t_{DVWH}	10	—	10	—	15	—	20	—	ns	
Data Hold TIme	t_{WHDX}	0	—	0	—	0	—	0	—	ns	
Write Low to Data High–Z	t_{WLQZ}	0	9	0	10	0	15	0	20	ns	4, 5, 6
Write High to Output Active	t_{WHQX}	5	—	5	—	5	—	5	—	ns	4, 5, 6
Write Recovery Time	t_{WHAX}	0	—	0	—	0	—	0	—	ns	

NOTES:
1. A write occurs during the overlap of $\overline{E}$ low and $\overline{W}$ low.
2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
3. All timings are referenced from the last valid address to the first transitioning address.
4. Transition is measured ± 500 mV from steady–state voltage with load of Figure 1B.
5. This parameter is sampled and not 100% tested.
6. At any given voltage and temperature, t_{WLQZ} max is less than t_{WHQX} min both for a given device and from device to device.

WRITE CYCLE 1 ($\overline{W}$ Controlled See Notes 1 and 2)

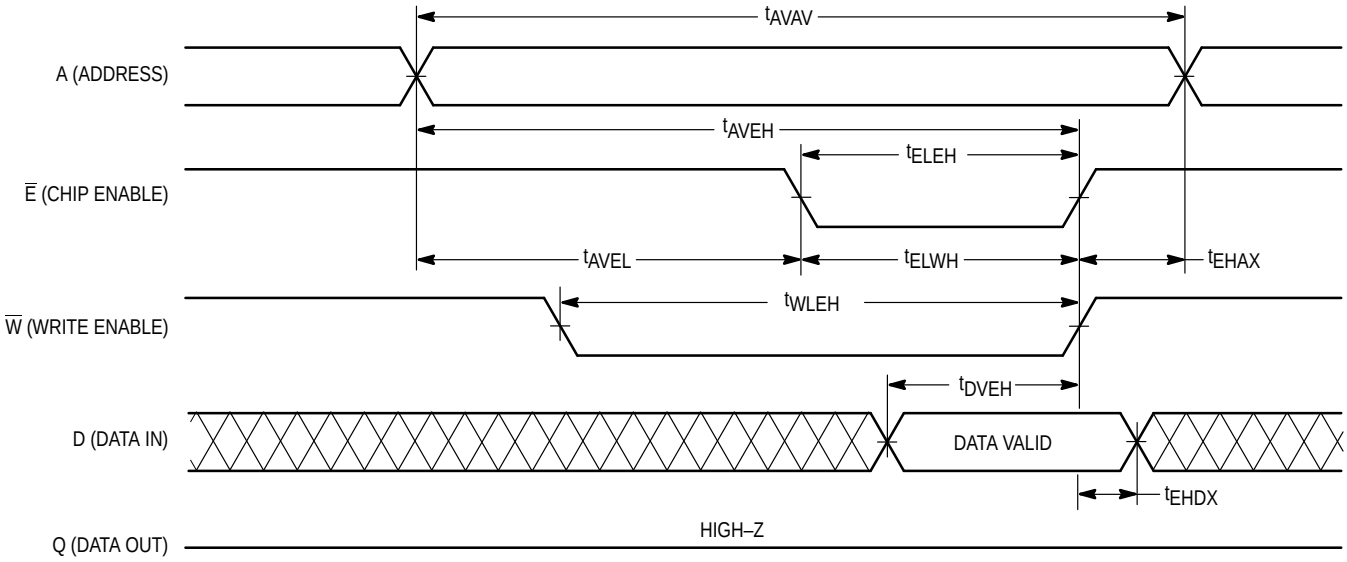


WRITE CYCLE 2 ($\overline{E}$ Controlled, See Notes 1 and 2)

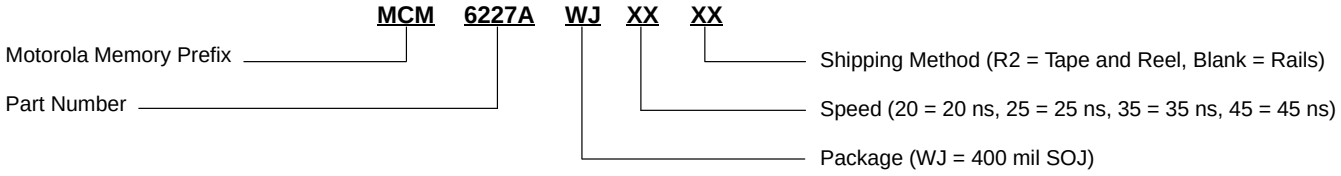
Parameter	Symbol	6227A–20		6227A–25		6227A–35		6227A–45		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max		
Write Cycle Time	t_{AVAV}	20	—	25	—	35	—	45	—	ns	3
Address Setup Time	t_{AVEL}	0	—	0	—	0	—	0	—	ns	
Address Valid to End of Write	t_{AVEH}	15	—	17	—	20	—	25	—	ns	
Enable to End of Write	t_{ELEH}, t_{ELWH}	15	—	17	—	20	—	25	—	ns	4, 5
Write Pulse Width	t_{WLEH}	15	—	17	—	20	—	25	—	ns	
Data Valid to End of Write	t_{DVEH}	10	—	10	—	15	—	20	—	ns	
Data Hold Time	t_{EHDX}	0	—	0	—	0	—	0	—	ns	
Write Recovery Time	t_{EHAX}	0	—	0	—	0	—	0	—	ns	

NOTES:
1. A write occurs during the overlap of $\overline{E}$ low and $\overline{W}$ low.
2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
3. All timings are referenced from the last valid address to the first transitioning address.
4. If $\overline{E}$ goes low coincident with or after $\overline{W}$ goes low, the output will remain in a high–impedance state.
5. If $\overline{E}$ goes high coincident with or before $\overline{W}$ goes high, the output will remain in a high–impedance state.

WRITE CYCLE 2 ($\overline{E}$ Controlled See Notes 1 and 2)



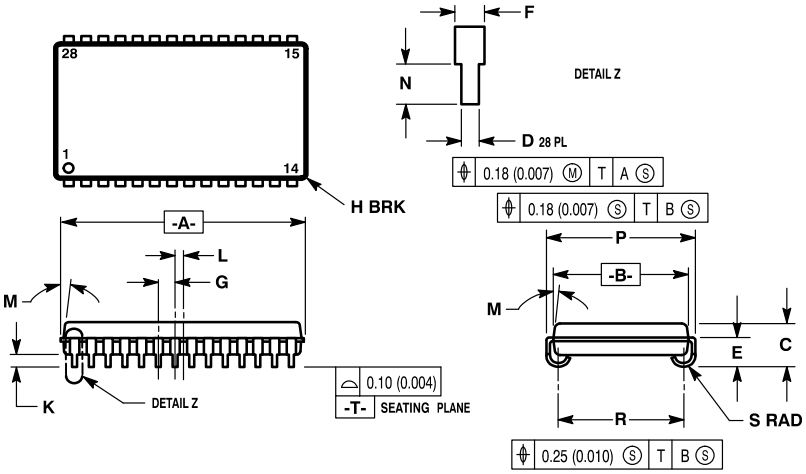
ORDERING INFORMATION
(Order by Full Part Number)



Full Part Numbers — MCM6227AWJ20 MCM6227AWJ20R2
MCM6227AWJ25 MCM6227AWJ25R2
MCM6227AWJ35 MCM6227AWJ35R2
MCM6227AWJ45 MCM6227AWJ45R2

PACKAGE DIMENSIONS

28 LEAD
400 MIL SOJ
CASE 810–03



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. DIMENSION A & B DO NOT INCLUDE MOLD PROTRUSION. MOLD PROTRUSION SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
3. CONTROLLING DIMENSION: INCH.
4. DIM R TO BE DETERMINED AT DATUM -T-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	18.29	18.54	0.720	0.730
B	10.04	10.28	0.395	0.405
C	3.26	3.75	0.128	0.148
D	0.39	0.50	0.015	0.020
E	2.24	2.48	0.088	0.098
F	0.67	0.81	0.026	0.032
G	1.27 BSC		0.050 BSC	
H	—	0.50	—	0.020
K	0.89	1.14	0.035	0.045
L	0.64 BSC		0.025 BSC	
M	0°	5°	0°	5°
N	0.76	1.14	0.030	0.045
P	11.05	11.30	0.435	0.445
R	9.15	9.65	0.360	0.380
S	0.77	1.01	0.030	0.040

Literature Distribution Centers:
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JAPAN: Nippon Motorola Ltd.; 4–32–1, Nishi–Gotanda, Shinagawa–ku, Tokyo 141, Japan.
ASIA PACIFIC: Motorola Semiconductors H.K. Ltd.; Silicon Harbour Center, No. 2 Dai King Street, Tai Po Industrial Estate, Tai Po, N.T., Hong Kong.